DEFECT MONITORING IN SEMICONDUCTOR DEVICE FABRICATION

ABSTRACT

A method of forming a device is presented. The method includes providing a substrate containing at least a partially formed device thereon. The device comprises at least one defect site. A pixilated image of the defect site is acquired, and each pixel comprises a grey level value (GLV). Surrounding noises of the defect site is eliminated. A point of the image is identified as the center of the defect. A plurality of iterations to exclude outer edge pixels surrounding the center of the defect image is performed. The defect is categorized as a killer or non-killer defect.

Fig. 5a